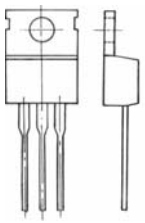
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220 Plastic-Encapsulate Transistors

MJE3055 TRANSISTOR (NPN)

TO-220

1. BASE
2. COLLECTOR
3. EMITTER



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FEATURES

Power dissipation

$P_{CM:}$ 2 W (Tamb=25℃)

Collector current

$I_{CM:}$ 10 A

Collector-base voltage

$V_{(BR)CBO}$: 70 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=1mA, I_E=0	70			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=200mA, I_B=0	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=70V, I_E=0			1	mA
Collector cut-off current	I_{CEO}	V_{CE}=30V, I_E=0			0.7	mA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			5	mA
DC current gain	$h_{FE(1)}$	V_{CE}=4V, I_C=4A	20		100	
	$h_{FE(2)}$	V_{CE}=4V, I_C=10A	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=4A, I_B=400mA			1.1	V
		I_C=10A, I_B=3.3A			8	V
Base-emitter voltage	V_{BE}	V_{CE}=4V, I_C=4A			1.8	V
Transition frequency	f_T	V_{CE}=10V, I_C=500mA		2		MHz